

MOS FIELD EFFECT TRANSISTOR 2SK3715

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3715 is N-channel MOS Field Effect Transistor designed for high current switching applications.

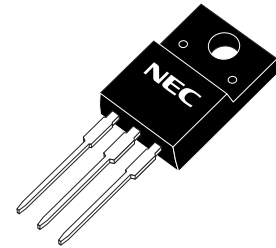
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3715	Isolated TO-220

FEATURES

- Super low on-state resistance
 $R_{DS(on)1} = 6.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 38 \text{ A)}$
 $R_{DS(on)2} = 9.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4 \text{ V, } I_D = 38 \text{ A)}$
- Low C_{iss} : $C_{iss} = 8400 \text{ pF TYP.}$
- Built-in gate protection diode

(Isolated TO-220)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 75	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 300	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	40	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	67	A
Single Avalanche Energy ^{Note2}	E_{AS}	450	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 30 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

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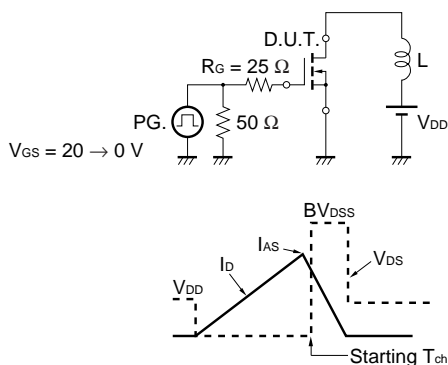
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

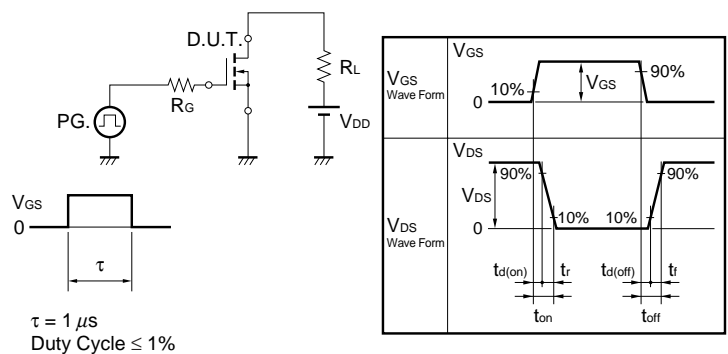
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 38 A	33	65		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 38 A		4.8	6.0	mΩ
	R _{DS(on)2}	V _{GS} = 4 V, I _D = 38 A		6.1	9.5	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		8400		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		1200		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		530		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30 V, I _D = 38 A		24		ns
Rise Time	t _r	V _{GS} = 10 V		15		ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		116		ns
Fall Time	t _f			11		ns
Total Gate Charge	Q _G	V _{DD} = 48 V		145		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		21		nC
Gate to Drain Charge	Q _{GD}	I _D = 75 A		39		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 75 A, V _{GS} = 0 V		0.92	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 50 A, V _{GS} = 0 V		59		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		136		nC

★ **Note** Pulsed

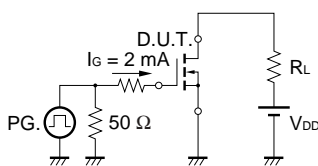
TEST CIRCUIT 1 AVALANCHE CAPABILITY



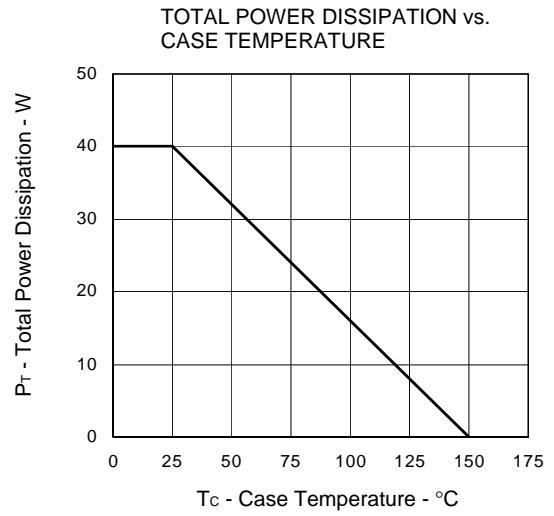
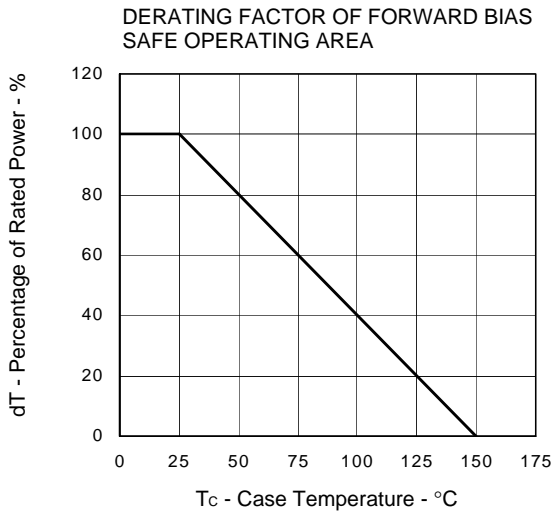
TEST CIRCUIT 2 SWITCHING TIME



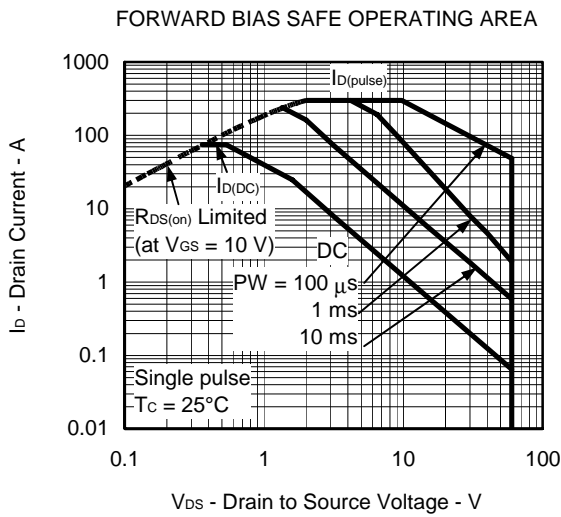
TEST CIRCUIT 3 GATE CHARGE



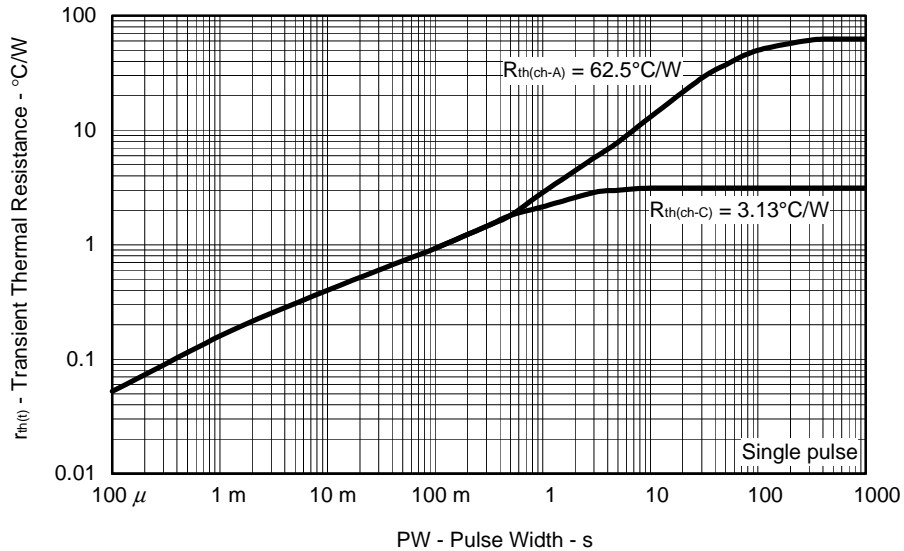
TYPICAL CHARACTERISTICS (T_A = 25°C)



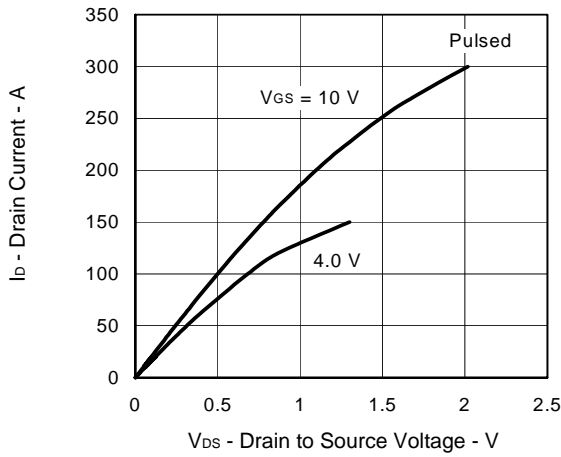
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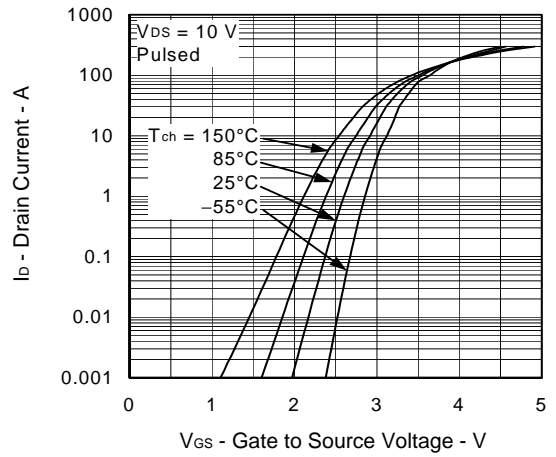
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



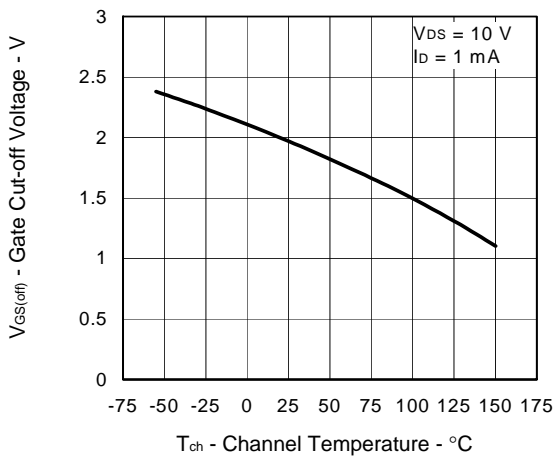
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



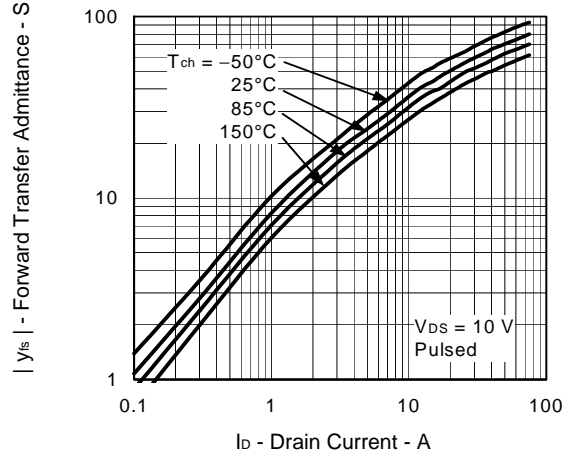
FORWARD TRANSFER CHARACTERISTICS



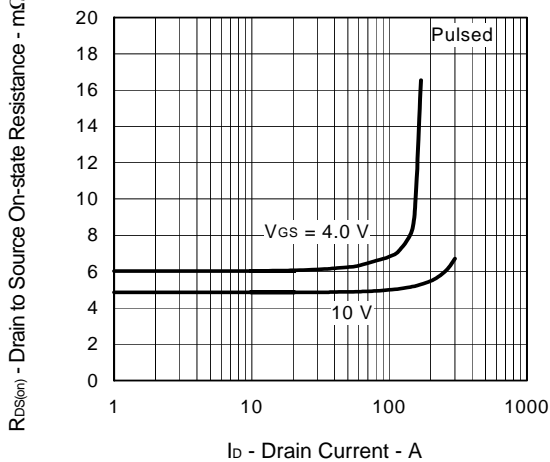
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



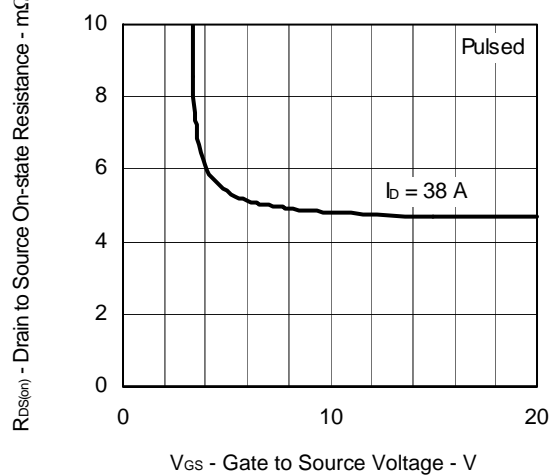
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



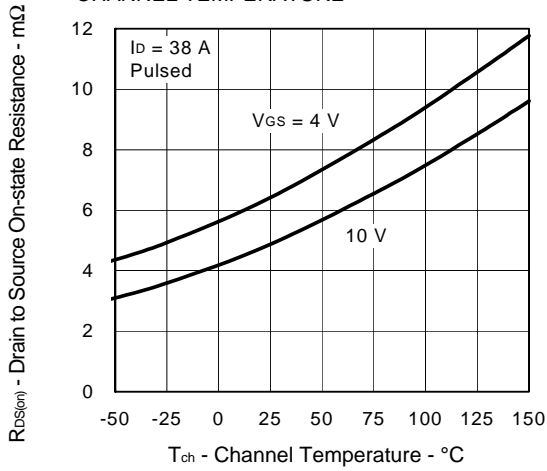
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



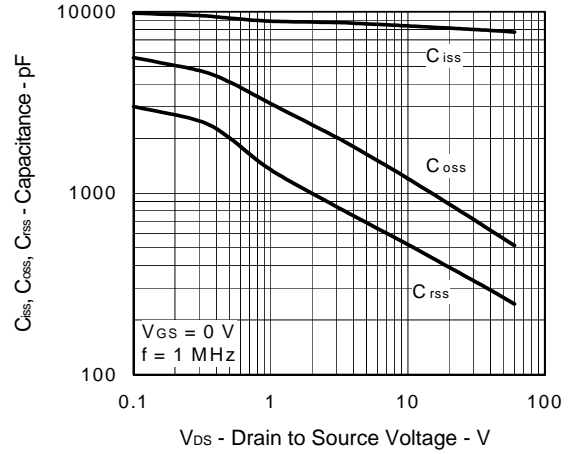
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



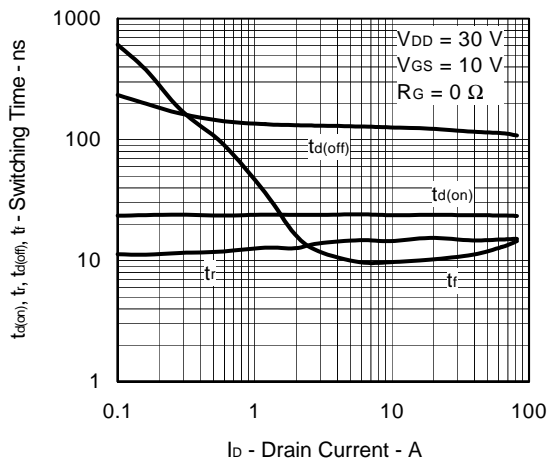
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



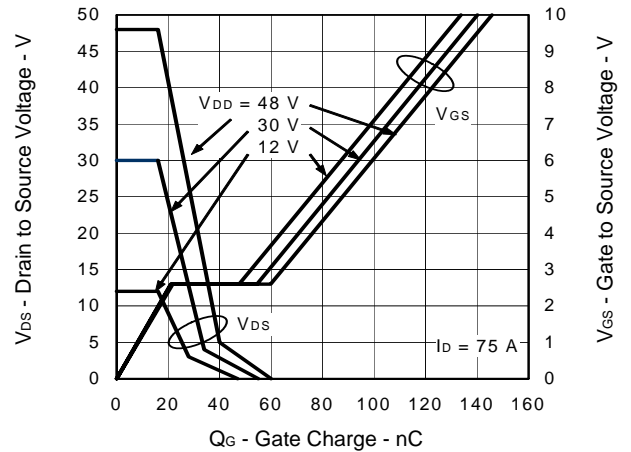
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



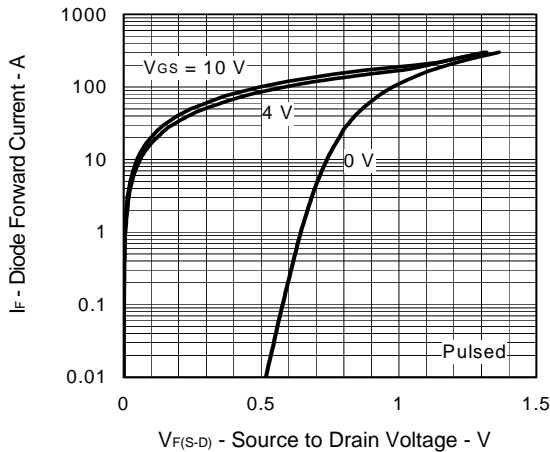
SWITCHING CHARACTERISTICS



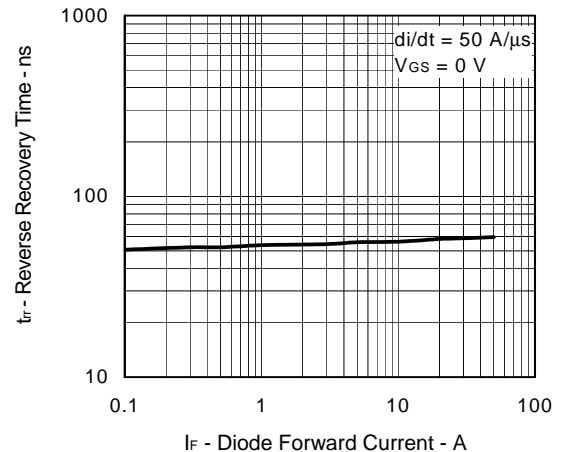
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



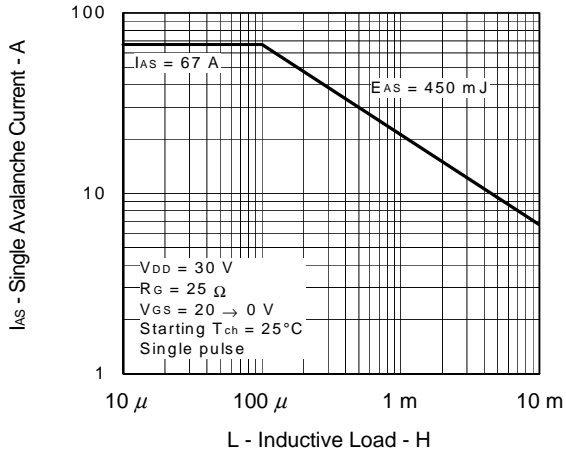
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



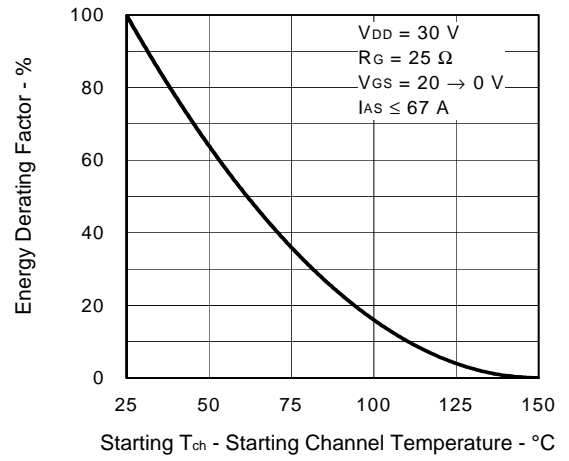
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

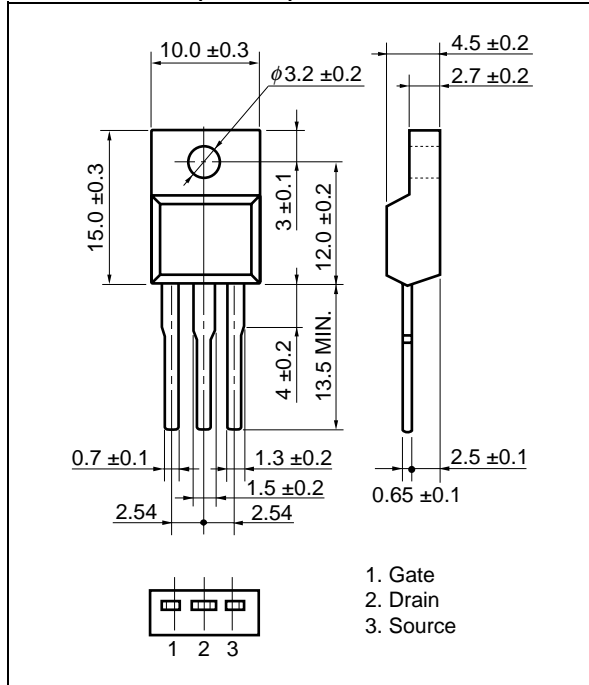


SINGLE AVALANCHE ENERGY DERATING FACTOR

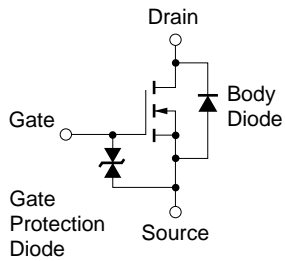


PACKAGE DRAWING (Unit: mm)

Isolated TO-220 (MP-45F)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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